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(54) **SEMICONDUCTOR DEVICE AND ELECTRONIC SYSTEM INCLUDING THE SAME**

(71) Applicant: **Samsung Electronics Co., Ltd.**, Suwon-si (KR)

(72) Inventors: **Hyunuk Jeon**, Osan-si (KR); **Yuseon Kang**, Hwaseong-si (KR); **Young-Min Ko**, Hwaseong-si (KR); **Dong Young Kim**, Pohang-si (KR)

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(57) **ABSTRACT**

Disclosed are a three-dimensional semiconductor memory device and an electronic system including the same. A semiconductor device includes a substrate, a cell array structure including a plurality of electrodes stacked on the substrate, a vertical channel structure that penetrates the cell array structure and is connected to the substrate, a conductive pad in an upper portion of the vertical channel structure, an interlayer insulating layer on the cell array structure, a bit line on the cell array structure, a bit line contact electrically connecting the bit line to the conductive pad, and a first stress release layer between the cell array structure and the bit line on a top surface of the interlayer insulating layer. The first stress release layer includes organosilicon polymer, and a carbon concentration of the first stress release layer is higher than that of the interlayer insulating layer.